

Trench gate field-stop IGBT M series, 650 V, 15 A low loss

Datasheet - production data

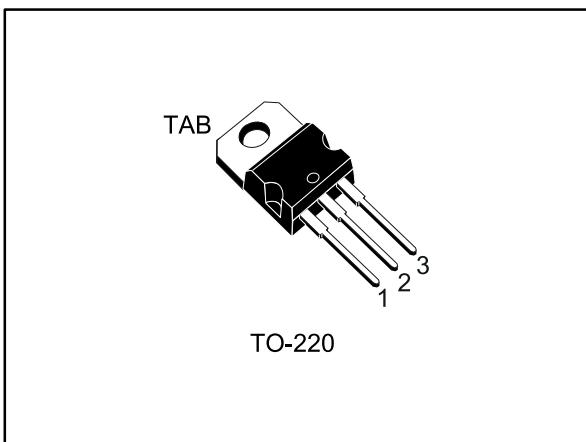
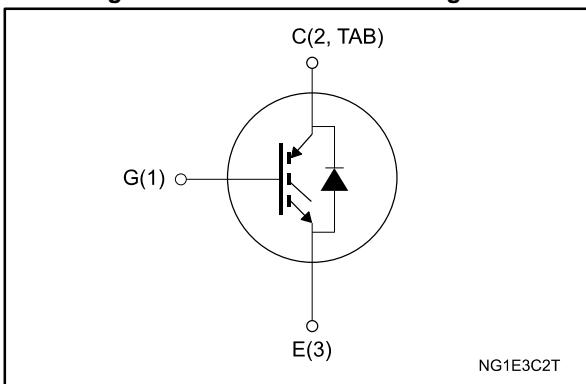


Figure 1: Internal schematic diagram



Features

- 6 μ s of short-circuit withstand time
- $V_{CE(sat)} = 1.55$ V (typ.) @ $I_c = 15$ A
- Tight parameter distribution
- Safer paralleling
- Low thermal resistance
- Soft and very fast recovery antiparallel diode

Applications

- Motor control
- UPS
- PFC

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series of IGBTs, which represent an optimum compromise in performance to maximize the efficiency of inverter systems where low-loss and short-circuit capability are essential. Furthermore, a positive $V_{CE(sat)}$ temperature coefficient and tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGP15M65DF2	G15M65DF2	TO-220	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$ V)	650	V
I_C	Continuous collector current at $T_C = 25$ °C	30	A
	Continuous collector current at $T_C = 100$ °C	15	
$I_{CP}^{(1)}$	Pulsed collector current	60	A
V_{GE}	Gate-emitter voltage	± 20	V
I_F	Continuous forward current at $T_C = 25$ °C	30	A
	Continuous forward current at $T_C = 100$ °C	15	
$I_{FP}^{(1)}$	Pulsed forward current	60	A
P_{TOT}	Total dissipation at $T_C = 25$ °C	136	W
T_{STG}	Storage temperature range	- 55 to 150	°C
T_J	Operating junction temperature	- 55 to 175	°C

Notes:

(1)Pulse width limited by maximum junction temperature.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case IGBT	1.1	°C/W
R_{thJC}	Thermal resistance junction-case diode	2.08	
R_{thJA}	Thermal resistance junction-ambient	62.5	

2 Electrical characteristics

$T_C = 25^\circ\text{C}$ unless otherwise specified

Table 4: Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0 \text{ V}, I_C = 2 \text{ mA}$	650			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE} = 15 \text{ V}, I_C = 15 \text{ A}$		1.55	2.0	V
		$V_{GE} = 15 \text{ V}, I_C = 15 \text{ A}, T_J = 125^\circ\text{C}$		1.9		
		$V_{GE} = 15 \text{ V}, I_C = 15 \text{ A}, T_J = 175^\circ\text{C}$		2.1		
V_F	Forward on-voltage	$I_F = 15 \text{ A}$		1.7		V
		$I_F = 15 \text{ A}, T_J = 125^\circ\text{C}$		1.5		
		$I_F = 15 \text{ A}, T_J = 175^\circ\text{C}$		1.4		
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 500 \mu\text{A}$	5	6	7	V
I_{CES}	Collector cut-off current	$V_{GE} = 0 \text{ V}, V_{CE} = 650 \text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			± 250	μA

Table 5: Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GE} = 0 \text{ V}$	-	1250	-	pF
C_{oes}	Output capacitance		-	80	-	
C_{res}	Reverse transfer capacitance		-	25	-	
Q_g	Total gate charge	$V_{CC} = 520 \text{ V}, I_C = 15 \text{ A}, V_{GE} = 15 \text{ V}$ (see Figure 30: "Gate charge test circuit")	-	45	-	nC
Q_{ge}	Gate-emitter charge		-	11	-	
Q_{gc}	Gate-collector charge		-	15	-	

Table 6: IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400 \text{ V}, I_C = 15 \text{ A}, V_{GE} = 15 \text{ V}, R_G = 12 \Omega$ (see Figure 29: "Test circuit for inductive load switching")		24	-	ns
t_r	Current rise time			7.8	-	ns
$(di/dt)_{on}$	Turn-on current slope			1570	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time			93	-	ns
t_f	Current fall time			106	-	ns
$E_{on}^{(1)}$	Turn-on switching losses			0.09	-	mJ
$E_{off}^{(2)}$	Turn-off switching losses			0.45	-	mJ
E_{ts}	Total switching losses			0.54	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400 \text{ V}, I_C = 15 \text{ A}, V_{GE} = 15 \text{ V}, R_G = 12 \Omega$ $T_J = 175 \text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching")		24.8	-	ns
t_r	Current rise time			9.2	-	ns
$(di/dt)_{on}$	Turn-on current slope			1300	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time			96	-	ns
t_f	Current fall time			169	-	ns
E_{on}	Turn-on switching losses			0.22	-	mJ
E_{off}	Turn-off switching losses			0.61	-	mJ
E_{ts}	Total switching losses			0.83	-	mJ
t_{sc}	Short-circuit withstand time	$V_{CC} \leq 400 \text{ V}, V_{GE} = 15 \text{ V}, T_{Jstart} = 150 \text{ }^\circ\text{C}$	6		-	μ s

Notes:

(1) Energy losses include reverse recovery of the diode.

(2) Turn-off losses also include the tail of the collector current.

Table 7: Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 15 \text{ A}, V_R = 400 \text{ V}, V_{GE} = 15 \text{ V}$ (see Figure 29: "Test circuit for inductive load switching") $di/dt = 1000 \text{ A}/\mu\text{s}$	-	142	-	ns
Q_{rr}	Reverse recovery charge		-	525	-	nC
I_{rrm}	Reverse recovery current		-	13.4	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	790	-	A/ μ s
E_{rr}	Reverse recovery energy		-	64	-	μ J
t_{rr}	Reverse recovery time		-	241	-	ns
Q_{rr}	Reverse recovery charge	$I_F = 15 \text{ A}, V_R = 400 \text{ V}, V_{GE} = 15 \text{ V}$ $T_J = 175 \text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching") $di/dt = 1000 \text{ A}/\mu\text{s}$	-	1690	-	nC
I_{rrm}	Reverse recovery current		-	20	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	420	-	A/ μ s
E_{rr}	Reverse recovery energy		-	176	-	μ J

2.1

Electrical characteristics (curves)

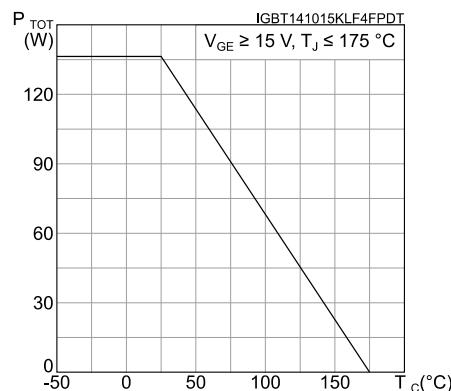
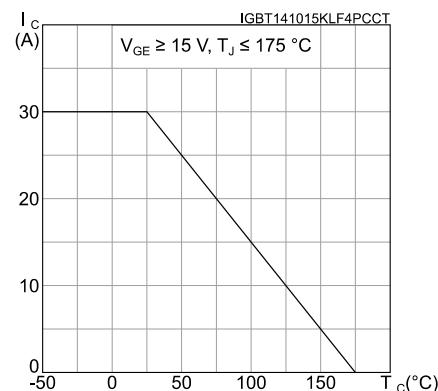
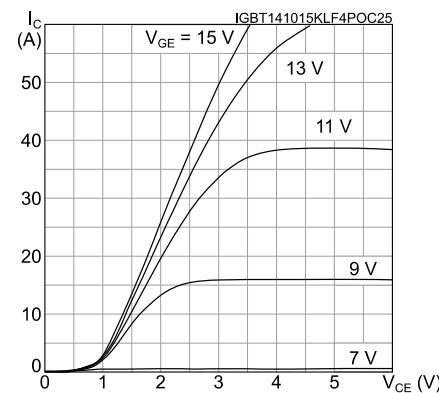
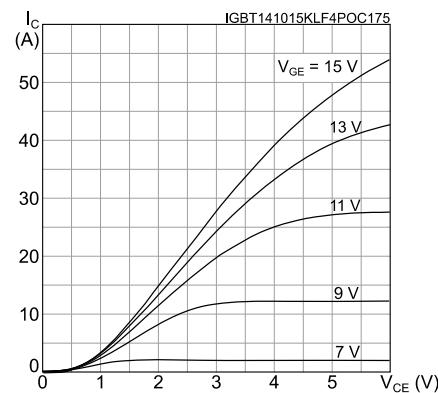
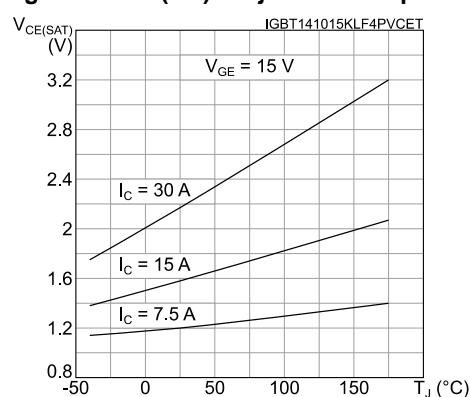
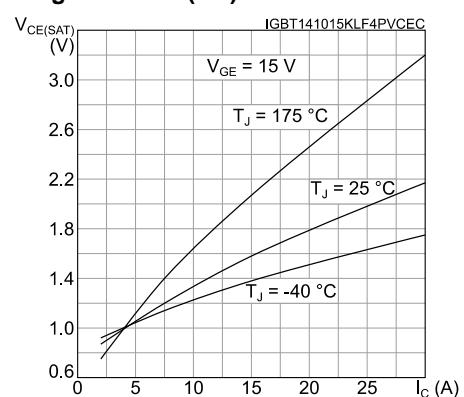
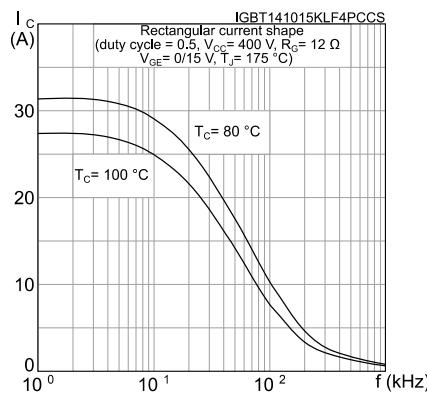
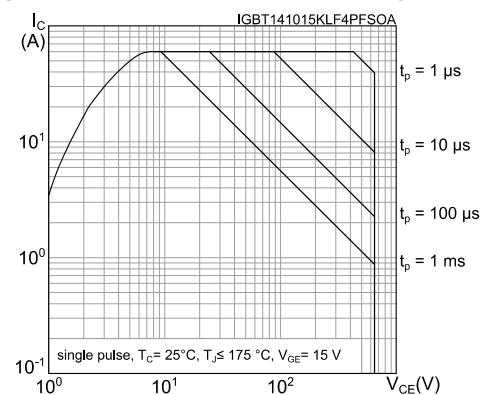
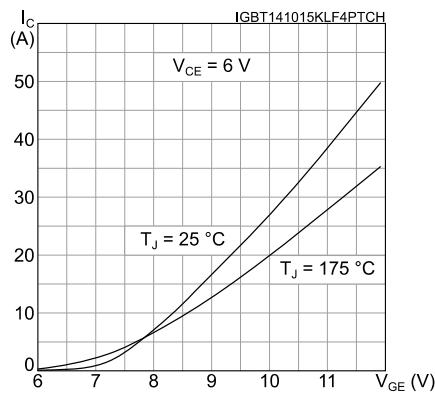
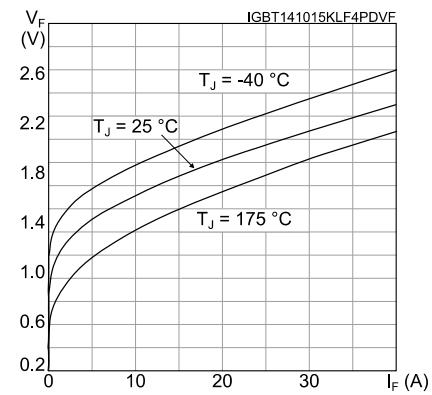
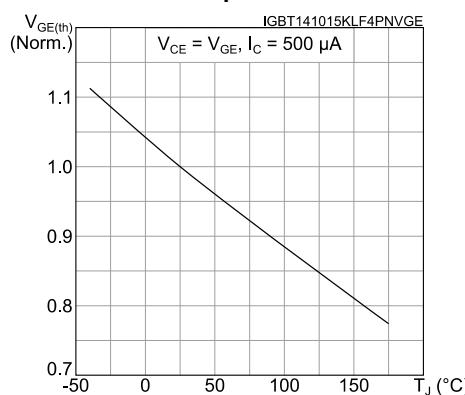
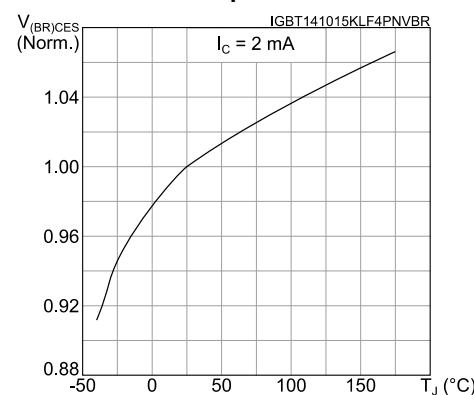
Figure 2: Power dissipation vs. case temperature**Figure 3: Collector current vs. case temperature****Figure 4: Output characteristics ($T_J = 25 \text{ }^{\circ}\text{C}$)****Figure 5: Output characteristics ($T_J = 175 \text{ }^{\circ}\text{C}$)****Figure 6: $V_{CE(\text{sat})}$ vs. junction temperature****Figure 7: $V_{CE(\text{sat})}$ vs. collector current**

Figure 8: Collector current vs. switching frequency**Figure 9: Forward bias safe operating area****Figure 10: Transfer characteristics****Figure 11: Diode VF vs. forward current****Figure 12: Normalized VGE(th) vs. junction temperature****Figure 13: Normalized V(BR)CES vs. junction temperature**

Electrical characteristics

STGP15M65DF2

Figure 14: Capacitance variations

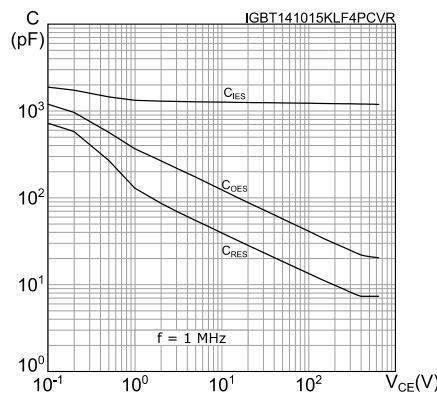


Figure 15: Gate charge vs. gate-emitter voltage

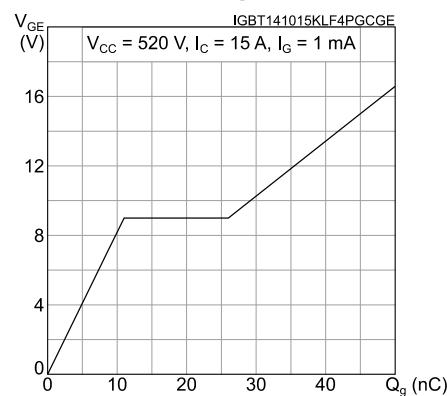


Figure 16: Switching loss vs. collector current

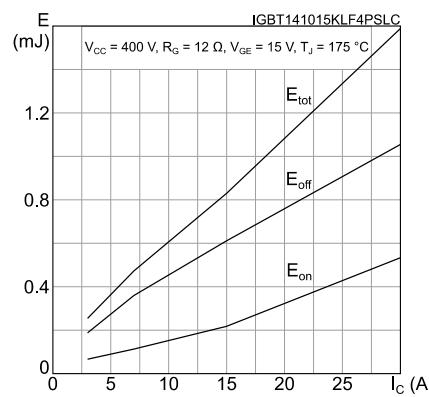


Figure 17: Switching loss vs. gate resistance

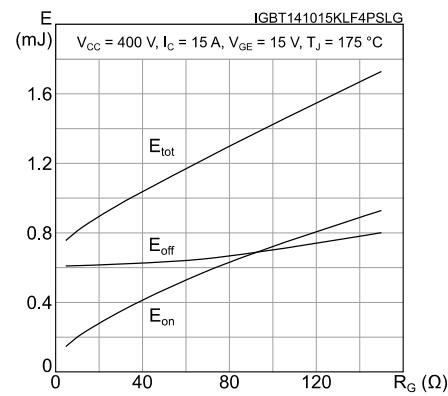


Figure 18: Switching loss vs. temperature

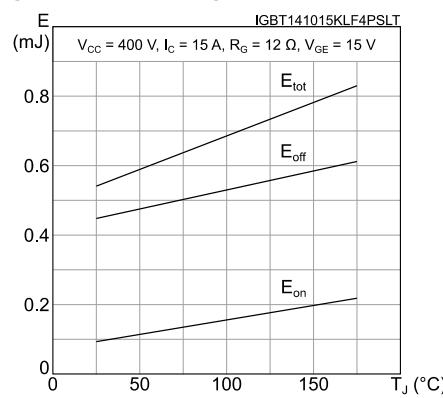


Figure 19: Switching loss vs. collector emitter voltage

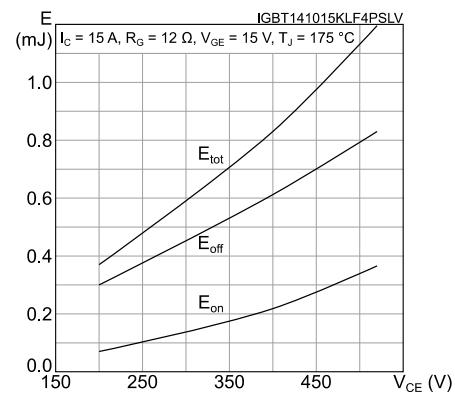


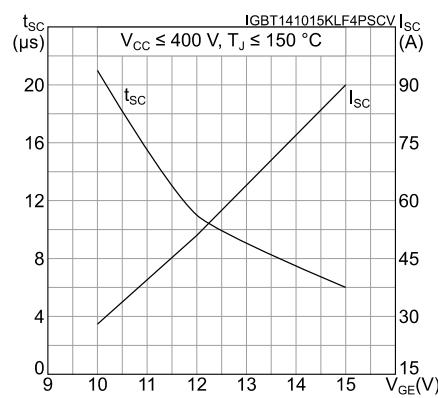
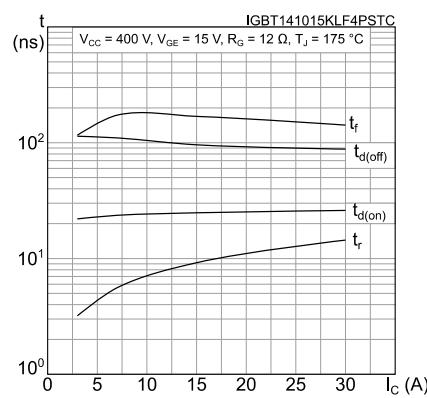
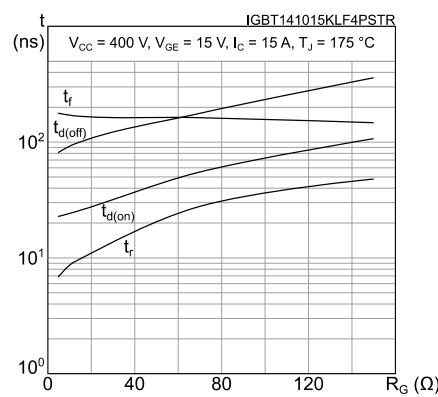
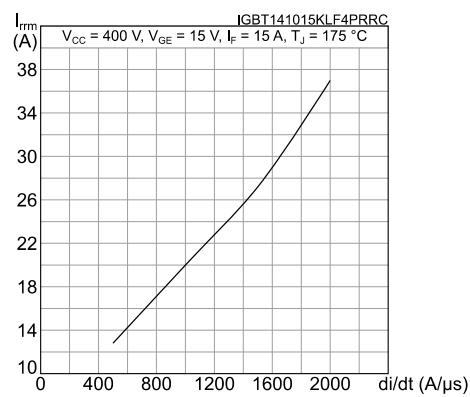
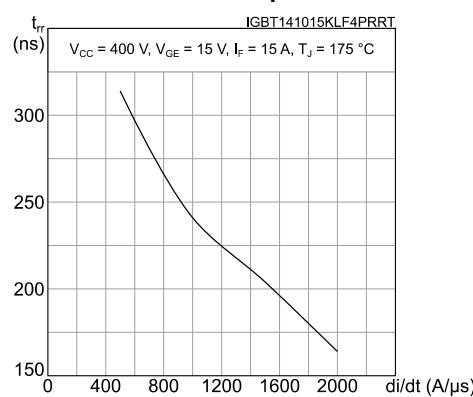
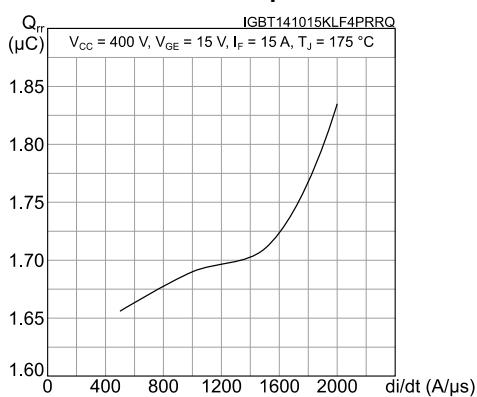
Figure 20: Short-circuit time and current vs. V_{GE}**Figure 21: Switching times vs. collector current****Figure 22: Switching times vs. gate resistance****Figure 23: Reverse recovery current vs. diode current slope****Figure 24: Reverse recovery time vs. diode current slope****Figure 25: Reverse recovery charge vs. diode current slope**

Figure 26: Reverse recovery energy vs. diode current slope

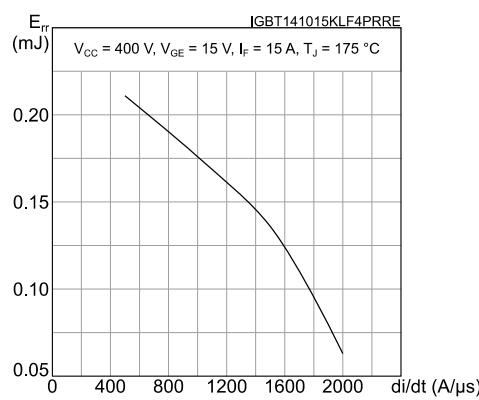


Figure 27: Thermal impedance for IGBT

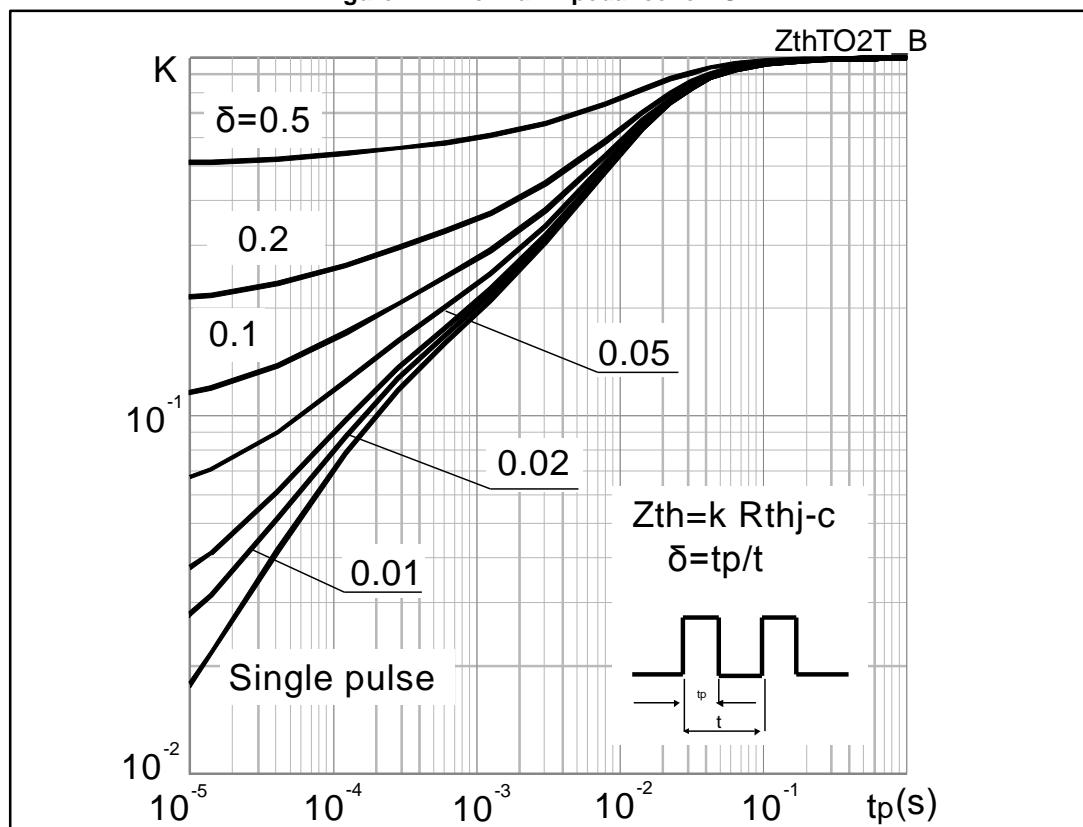
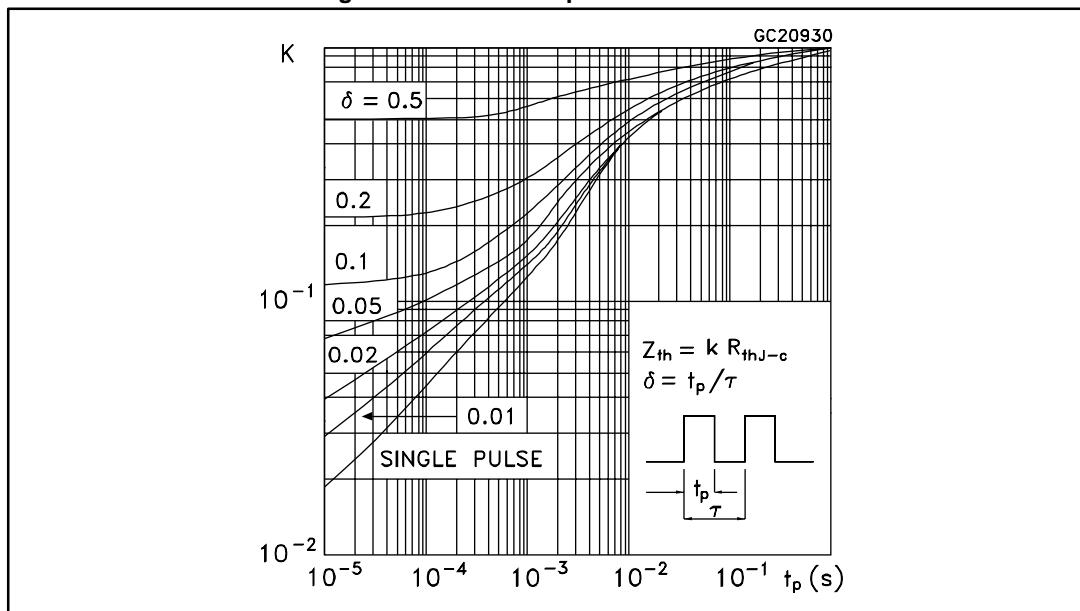


Figure 28: Thermal impedance for diode



3 Test circuits

Figure 29: Test circuit for inductive load switching

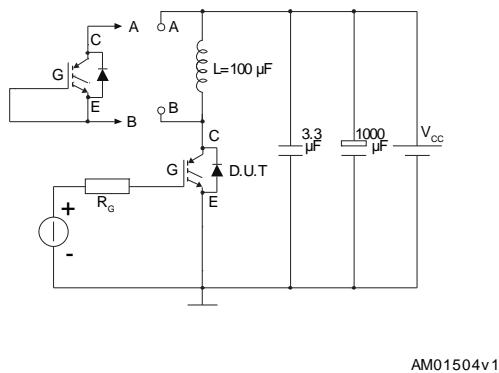


Figure 30: Gate charge test circuit

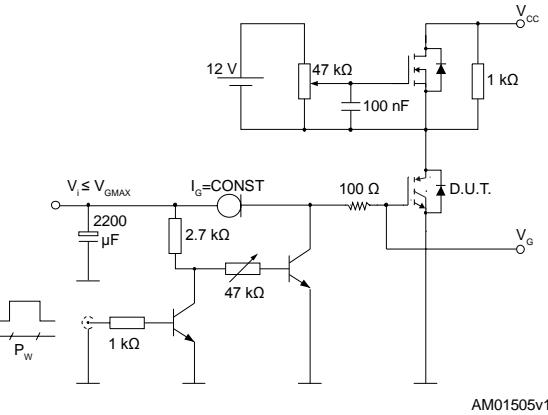


Figure 31: Switching waveform

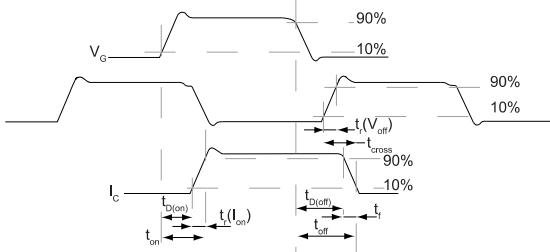
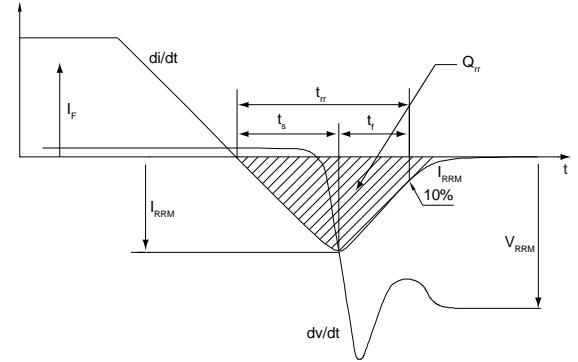


Figure 32: Diode reverse recovery waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

4.1 TO-220 type A package information

Figure 33: TO-220 type A package outline

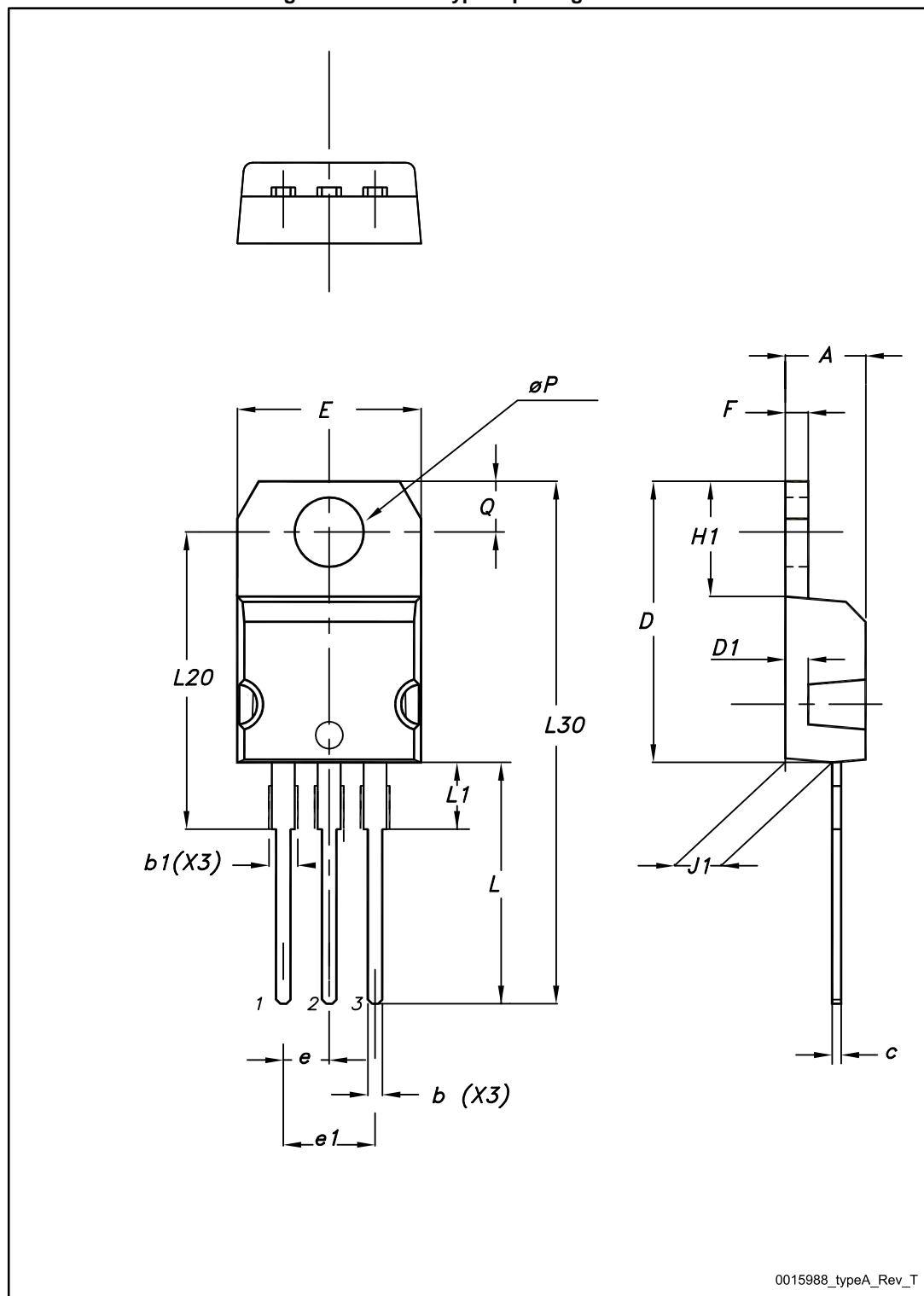


Table 8: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

5 Revision history

Table 9: Document revision history

Date	Revision	Changes
14-Oct-2015	1	First release.
13-Nov-2015	2	Document status promoted from preliminary to production data.

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